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⌘ Title: **TW0452872B: METHOD OF CONTROLLING THICKNESS OF SCREEN OXIDE LAYER**

⌘ Country: **TW Taiwan**⌘ Kind: **B Patent**

⌘ Inventor: **WU, JAU-JIUE; Taiwan**
HU, JU-JIUN; Taiwan

⌘ Assignee: **PROMOS TECHNOLOGIES INC. Taiwan**
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Filed:

⌘ Application **TW2000089115478**

Number:

⌘ IPC Code: **H01L 21/283;**⌘ ECLA Code: **None**⌘ Priority **2000-08-02 TW2000089115478**

Number:

⌘ Abstract:

This invention provides a method to control the thickness of the screen oxide layer. On a given substrate, there is a gate located on a pre-determined area of the substrate surface. A screen oxide layer is placed on the substrate surface to surround the gate. An insulation layer is used to cover the gate and the screen oxide layer. Subsequently, an anisotropic dry etch process is employed to remove the insulation layer on top of the gate surface and the substrate surface. The remaining insulation layer on the side wall of the gate forms a gate spacer. A wet etch process using a dilute hydrofluoric acid is then performed to etch the screen oxide layer uncovered by the spacer to a pre-determined thickness.

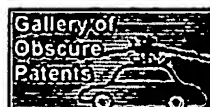

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⌘ Family:

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⌘ Other Abstract
Info:

None

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